

NCD15S10WC

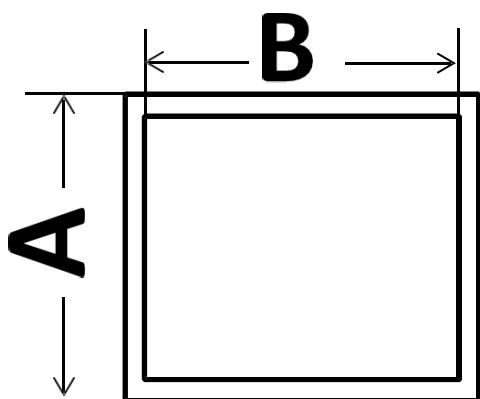
Trench Schottky Barrier Diode Wafer (TSBD)

Maximum Ratings @ $T_A=25^{\circ}\text{C}$ (unless otherwise specified)

Parameter	Symbol	Ratings	Units
Working Peak Reverse Voltage	V_{RWM}	150	V
Average Rectified Forward	$I_{F(AV)}$	10	A
Non-repetitive Peak Surge Current (8.3ms, half sine wave) Rated load (JEDEC METHOD)	I_{FSM}	220	A
Operating Junction Temperature	T_J	175	$^{\circ}\text{C}$

Electrical Characteristics @ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Breakdown Voltage	V_{BR}	$I_R=0.05\text{mA}$	150	-	-	V
Forward Voltage Drop	V_F	$I_F=10\text{A}$	-	-	0.80	V
		$I_F=15\text{A}$		-	0.87	V
Reverse Leakage Current	I_R	$V_R=150\text{V}$	-	-	10	μA



Item	Information
Die Size (A)	2387 μm
Top Metal Pad Size (B)	2397 μm
Passivation Seal	2327 μm
Wafer Thickness	240 μm
Gross Die Scribe Line Width	60 μm
Top Metal	Al
Back Metal	Ag
Gross Die	2730
Wafer Size	6"